

GaAs TSQB structures

NIST

3nm InAs cap

121nm InAlAs

121nm InAlAs

750nm InGaAs

$\text{In}_{0.52}\text{Al}_{0.48}\text{As}$

$\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$

3.75 mL GaAs QDs (M445)

534

M445

Fe: InP(III)A semi-ins.

Large piece (~ 1/2 wafer)

PARIS

3nm InAs cap

200nm $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$

3.75ML GaAs QDs

200nm $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$

50nm $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$

InP(III)A semi-ins.

4.00 mL GaAs QDs

~ 1/4 wafer.

As4

Do we need etch samples.

Tasks

1. check InAlAs, InGaAs compositions are good - if not, grow tests
2. Make sure GaAs growth rate for QDs is locked in - if not, R10s.
3. Make sure growth rates converted to (111).